ABSTRACT

The present invention relates to a method for fabricating a thin film transistor liquid crystal display, which comprises the steps of: forming a gate electrode on an insulating substrate; successively forming first and second insulating films on the insulating substrate including the gate electrode, the first insulating film being formed under first deposition conditions including power, pressure and electrode interval, the second insulating film being formed under second deposition conditions where at least one of the first deposition conditions is changed continuously over time; successively forming first and second amorphous silicon layers on the second insulating film to form an active layer; successively forming an ohmic contact layer and a source/drain electrode on the active layer; and forming a protective film on the resulting structure including the source/drain electrode.